



09/135413

**PATENT**

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

Applicant:	Leonard Forbes et al.	Examiner:	Viet Nguyen
Serial No.:	09/135,413	Group Art Unit:	2818
Filed:	August 14, 1998	Docket:	303.354US2
Title:	METHOD FOR OPERATING A DEAPROM HAVING AN AMORPHOUS SILICON CARBIDE GATE INSULATOR		

**INFORMATION DISCLOSURE STATEMENT**

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

In compliance with the duty imposed by 37 C.F.R. § 1.56, and in accordance with 37 C.F.R. §§ 1.97 *et. seq.*, the enclosed materials are brought to the attention of the Examiner for consideration in connection with the above-identified patent application. Applicants respectfully request that this Information Disclosure Statement be entered and the documents listed on the attached Form 1449 be considered by the Examiner and made of record. Pursuant to the provisions of MPEP 609, Applicants request that a copy of the 1449 form, initialed as being considered by the Examiner, be returned to the Applicants with the next official communication.

Pursuant to 37 C.F.R. §1.97(b), it is believed that no fee or statement is required with the Information Disclosure Statement. However, if an Office Action on the merits has been mailed, the Commissioner is hereby authorized to charge the required fees to Deposit Account No. 19-0743 in order to have this Information Disclosure Statement considered.

INFORMATION DISCLOSURE STATEMENT

Serial No :09/135413

Filing Date: August 14, 1998

Title: METHOD FOR OPERATING A DEAPROM HAVING AN AMORPHOUS SILICON CARBIDE GATE INSULATOR

Page 2

Dkt: 303.354US2


The Examiner is invited to contact the Applicants' Representative at the below-listed telephone number if there are any questions regarding this communication.

Respectfully submitted,

LEONARD FORBES ET AL.

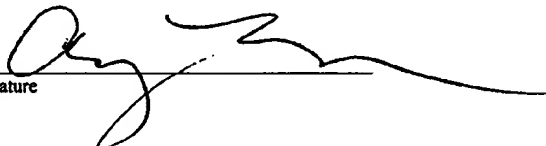
By their Representatives,

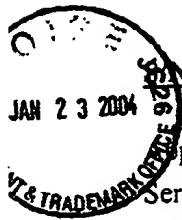
SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A.  
P.O. Box 2938  
Minneapolis, MN 55402  
(612) 373-6973

Date 21 JANUARY 2004 By   
Robert E. Mates  
Reg. No. 35,271

CERTIFICATE UNDER 37 CFR 1.8: The undersigned hereby certifies that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail, in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on this 21<sup>st</sup> day of January, 2004.

Name Amy Moriarty

Signature 



09/135413

**PATENT****IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

Applicant: Leonard Forbes et al.

Examiner: Viet Nguyen

Serial No.: 09/135413

Group Art Unit: 2818

Filed: August 14, 1998

Docket: 303.354US2

Title: METHOD FOR OPERATING A MEMORY DEVICE HAVING AN  
AMORPHOUS SILICON CARBIDE GATE INSULATOR**COMMUNICATION CONCERNING RELATED APPLICATION(S)**

MS RCE

Commissioner for Patents

P.O. Box 1450

Alexandria, VA 22313-1450

Applicants would like to bring to the Examiner's attention the following related application(s) in the above-identified patent application:

<u>Serial/Patent No.</u>	<u>Filing Date</u>	<u>Attorney Docket</u>	<u>Title</u>
09/652420	August 31, 2000	303.324US3	TRANSISTOR WITH VARIABLE ELECTRON AFFINITY GATE AND METHODS OF FABRICATION AND USE
09/691004	October 18, 2000	303.324US4	TRANSISTOR WITH VARIABLE ELECTRON AFFINITY GATE AND METHODS OF FABRICATION AND USE
08/903486	July 29, 1997	303.326US1	SILICON CARBIDE GATE TRANSISTOR
09/259870	March 1, 1999	303.326US2	FABRICATION OF SILICON CARBIDE GATE TRANSISTOR
08/902132 5886368	July 29, 1997	303.353US1	TRANSISTOR WITH SILICON OXYCARBIDE GATE AND METHODS OF FABRICATION AND USE
09/138294 6309907	August 21, 1998	303.353US2	TRANSISTOR WITH SILICON OXYCARBIDE GATE AND METHODS OF FABRICATION AND USE
08/902843	July 29, 1997	303.354US1	DEAPROM HAVING AMORPHOUS SILICON CARBIDE GATE

COMMUNICATION CONCERNING RELATED APPLICATIONS

Serial Number: 09/135413

Filing Date: August 14, 1998

Title: METHOD FOR OPERATING A MEMORY DEVICE HAVING AN AMORPHOUS SILICON CARBIDE GATE INSULATOR

Page 2  
Dkt: 303.354US2

INSULATOR

09/134713	August 14, 1998	303.354US3	DEAPROM HAVING AMORPHOUS SILICON CARBIDE GATE INSULATOR
08/902098 6031263	July 29, 1997	303.355US1	DEAPROM AND TRANSISTOR WITH GALLIUM NITRIDE OR GALLIUM ALUMINUM NITRIDE GATE
09/140978 6307775	August 27, 1998	303.355US2	DEAPROM AND TRANSISTOR WITH GALLIUM NITRIDE OR GALLIUM ALUMINUM NITRIDE GATE
09/141392 6249020	August 27, 1998	303.355US3	DEAPROM AND TRANSISTOR WITH GALLIUM NITRIDE OR GALLIUM ALUMINUM NITRIDE GATE
09/883795	June 18, 2001	303.355US4	DEAPROM AND TRANSISTOR WITH GALLIUM NITRIDE OR GALLIUM ALUMINUM NITRIDE GATE
10/047181	October 23, 2001	303.355US5	MEMORY DEVICE WITH GALLIUM NITRIDE OR GALLIUM ALUMINUM NITRIDE GATE
08/902133	July 29, 1997	303.356US1	MEMORY DEVICE
10/231687	August 29, 2002	303.356US2	DYNAMIC ELECTRICALLY ALTERABLE PROGRAMMABLE READ ONLY MEMORY DEVICE
08/903453	July 29, 1997	303.378US1	CARBURIZED SILICON GATE INSULATORS FOR INTEGRATED CIRCUITS
09/258467	February 26, 1999	303.378US2	CARBURIZED SILICON GATE INSULATORS FOR INTEGRATED CIRCUITS

COMMUNICATION CONCERNING RELATED APPLICATIONS

Serial Number: 09/135413

Filing Date: August 14, 1998

Title: METHOD FOR OPERATING A MEMORY DEVICE HAVING AN AMORPHOUS SILICON CARBIDE GATE INSULATOR

Page 3  
Dkt: 303.354US2


09/650553	August 30, 2000	303.378US3	CARBURIZED SILICON GATE INSULATORS FOR INTEGRATED CIRCUITS
10/461593	June 11, 2003	303.356US3	DYNAMIC ELECTRICALLY ALTERABLE PROGRAMMABLE READ ONLY MEMORY DEVICE
	Herewith	303.356US4	DYNAMIC ELECTRICALLY ALTERABLE PROGRAMMABLE READ ONLY MEMORY DEVICE

Respectfully submitted,

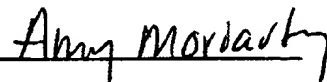
LEONARD FORBES ET AL.

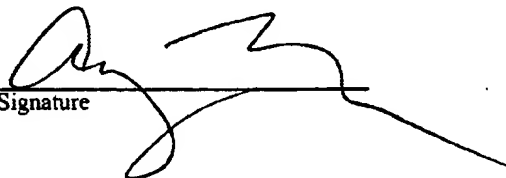
By Applicants' Representatives,

SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A.  
P.O. Box 2938  
Minneapolis, MN 55402  
(612) 373-6973

Date 21 JANUARY 2004 By   
Robert E. Mates  
Reg. No. 35,271

CERTIFICATE UNDER 37 CFR 1.8: The undersigned hereby certifies that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail, in an envelope addressed to: MS RCE, Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on this 21<sup>st</sup> day of January, 2004.

  
Name

  
Signature

Substitute for form 1449A/PTO

**INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT**  
(Use as many sheets as necessary)



Sheet 1 of 1

<b>Complete if Known</b>	
Application Number	09/135,413
Filing Date	August 14, 1998
First Named Inventor	Forbes, Leonard
Group Art Unit	2818
Examiner Name	Nguyen, Viet
Attorney Docket No: 303.354US2	

**US PATENT DOCUMENTS**

Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date if Appropriate
	US-4,598,305	07/01/1986	Chiang, A., et al.	357	23.7	06/18/1984
	US-4,980,303	12/25/1990	Yamauchi, T.	437	31	08/18/1988
	US-4,994,401	02/19/1991	Ukai, Y.	437	40	03/26/1990
	US-5,189,504	02/23/1993	Nakayama, S., et al.	257	422	01/30/1992
	US-5,336,361	08/09/1994	Tamura, A., et al.	438	767	11/02/1992
	US-5,367,306	11/22/1994	Hollon, , et al.	342	386	06/04/1993
	US-5,409,501	04/25/1995	Zauns-Huber, R., et al.	8	94.29	07/06/1992
	US-5,990,531	11/23/1999	Taskar, N. R., et al.	257	410	11/12/1997
	US-6,100,193	08/08/2000	Suehiro, S., et al.	438	685	09/24/1997
	US-6,166,768	12/26/2000	Fossum, , et al.	348	308	01/22/1997
	US-6,365,919	04/02/2002	Tihanyi, J., et al.	257	77	07/11/2000

**FOREIGN PATENT DOCUMENTS**

Examiner Initials *	Foreign Document No	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	T <sup>2</sup>
	JP-60-024678	02/07/1985	Akio, Nakatani	G06 K	9/36	

**OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS**

Examiner Initials *	Cite No *	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
		NAKAMURA, J., et al., "CMOS Active Pixel Image Sensor with Simple Floating Gate Pixels", IEEE Transactions on Electron Devices, 42, (1995), 1693-1694	
		WOLF, S., Silicon Processing for the VLSI Era, Vol. 3, Lattice Press, Sunset Beach, CA, (1995), 311-312	

**EXAMINER**

**DATE CONSIDERED**

Substitute Disclosure Statement Form (PTO-1449)

\* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. Applicant's unique citation designation number (optional) : Applicant is to place a check mark here if English language Translation is attached